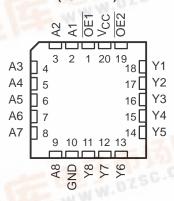
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- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static-Power Dissipation
- I_{off} and Power-Up 3-State Support Hot Insertion
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce)
 < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Package, and Ceramic (J) DIPs

SN54LVTH540 . . . J OR W PACKAGE SN74LVTH540 . . . DB, DW, OR PW PACKAGE (TOP VIEW)



SN54LVTH540 ... FK PACKAGE (TOP VIEW)



description

These octal buffers/drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVTH540 devices are ideal for driving bus lines or buffer memory address registers. These devices feature inputs and outputs on opposite sides of the package that facilitate printed circuit board layout.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable (OE1 or OE2) input is high, all outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When V_{CC} is between 0 and 1.5 V, the devices are in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

These devices are fully specified for hot-insertion applications using I_{off} and power-up 3-state. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



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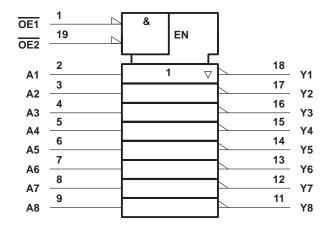
description (continued)

The SN54LVTH540 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH540 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

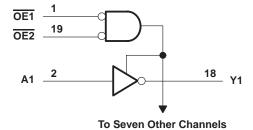
	OUTPUT		
OE1	OE2	Α	Y
L	L	L	Н
L	L	Н	L
Н	X	Χ	Z
Х	Н	Χ	Z

logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	
Input voltage range, V _I (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the high-impedance	
or power-off state, V _O (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the high state, V _O (see Note 1)	0.5 V to V _{CC} + 0.5 V
Current into any output in the low state, I _O : SN54LVTH540	96 mA
SN74LVTH540	
Current into any output in the high state, I _O (see Note 2): SN54LVTH540	48 mA
SN74LVTH540	64 mA
Input clamp current, I _{IK} (V _I < 0)	–50 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Package thermal impedance, θ _{JA} (see Note 3): DB package	115°C/W
DW package	97°C/W
PW package	128°C/W
Storage temperature range, T _{Stg}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

- 2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
- 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

		SN54LVTH540		SN74LVTH540		UNIT
		MIN	MAX	MIN	MAX	UNIT
Vcc	Supply voltage	2.7	3.6	2.7	3.6	V
VIH	High-level input voltage	2	N.	2		V
V _{IL}	Low-level input voltage		0.8		0.8	V
VI	Input voltage	į	5.5		5.5	V
ІОН	High-level output current	6	-24		-32	mA
l _{OL}	Low-level output current	32	48		64	mA
Δt/Δν	Input transition rise or fall rate	0	10		10	ns/V
Δt/ΔV _{CC}	Power-up ramp rate	200		200		μs/V
T _A	Operating free-air temperature	-55	125	-40	85	°C

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN	SN54LVTH540			SN74LVTH540					
		TEST CONDITIONS			TYP†	MAX	MIN	TYP†	MAX	UNIT			
VIK		$V_{CC} = 2.7 \text{ V},$	I _I = -18 mA			-1.2			-1.2	V			
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V},$	$I_{OH} = -100 \mu A$	V _{CC} -0	.2		V _{CC} -0	.2		V			
		$V_{CC} = 2.7 \text{ V},$	$I_{OH} = -8 \text{ mA}$	2.4			2.4						
VOH		VCC = 3 V	$I_{OH} = -24 \text{ mA}$	2						ı v			
		VCC = 3 V	$I_{OH} = -32 \text{ mA}$				2						
		V _{CC} = 2.7 V	I _{OL} = 100 μA			0.2			0.2				
		VCC = 2.7 V	I _{OL} = 24 mA			0.5			0.5	· v			
V _{OL}			I _{OL} = 16 mA			0.4			0.4				
VOL		V _{CC} = 3 V	$I_{OL} = 32 \text{ mA}$			0.5			0.5				
		\(\(\text{CC} = 3\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	$I_{OL} = 48 \text{ mA}$			0.55							
	-		I _{OL} = 64 mA				0.55						
		$V_{CC} = 0 \text{ or } 3.6 \text{ V},$	V _I = 5.5 V			<u>\$</u> 10							
١.	Control inputs	V _{CC} = 3.6 V,	$V_I = V_{CC}$ or GND		Š	±1			±1	±1 μΑ			
l II	5	V _{CC} = 3.6 V	$V_I = V_{CC}$		1				1	μΑ			
	Data inputs		V _I = 0		1	– 5			– 5				
l _{off}		$V_{CC} = 0$,	V_I or $V_O = 0$ to 4.5 V		2				±100	μΑ			
		VCC = 3 V	V _I = 0.8 V	750		75							
I _{I(hold)}	Data inputs		V _I = 2 V	-75			-75			μΑ			
		$V_{CC} = 3.6 V^{\ddagger}$,	$V_{I} = 0 \text{ to } 3.6 \text{ V}$						±500)0			
lozh		$V_{CC} = 3.6 \text{ V},$	V _O = 3 V			5			5	μΑ			
lozL		V _{CC} = 3.6 V,	$V_0 = 0.5 V$			- 5			– 5	μΑ			
$V_{CC} = 0 \text{ to } 1.5 \text{ V, } V_{O} = 0.9 $ $OE = \text{don't care}$).5 V to 3 V,			±100*			±100	μΑ				
I_{OZPD} $\frac{V_{CC}}{OE} = 1.5 \text{ V to } 0, V_{O} = 0.5 \text{ V}$		0.5 V to 3 V,			±100*			±100	μΑ				
Icc		V _{CC} = 3.6 V,	Outputs high			0.19		0.19					
		$I_{O} = 0$,	Outputs low			5			5	5 mA			
		$V_I = V_{CC}$ or GND	Outputs disabled			0.19			0.19				
ΔICC§		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$, One input at $V_{CC} - 0.6 \text{ V}$, Other inputs at V_{CC} or GND				0.2			0.2	mA			
C _i		V _I = 3 V or 0			3			3		pF			
Co		V _O = 3 V or 0			7			7		pF			

^{*} On products compliant to MIL-PRF-38535, this parameter is not production tested.



[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C. ‡ This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another. § This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

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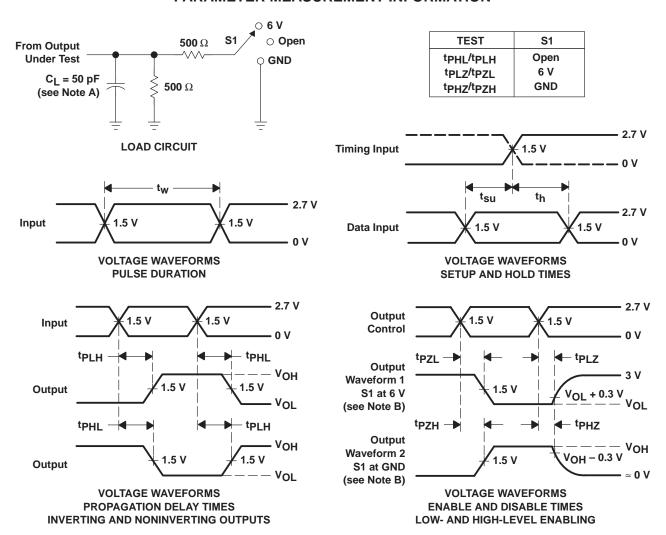
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L = 50$ pF (unless otherwise noted) (see Figure 1)

		TO (OUTPUT)	SN54LVTH540			SN74LVTH540							
PARAMETER	FROM (INPUT)		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V			V _{CC} = 2.7 V		UNIT	
			MIN	MAX	MIN	MAX	MIN	TYP	MAX	MIN	MAX		
^t PLH	А	~	1	3.9	NA	4.7	1.1	2.4	3.8		4.6	ns	
^t PHL		'	1	3.9	YY	4.7	1.1	2.7	3.8		4.6	115	
^t PZH	OE1 or OE2	~	1.4	5.3	1,	6.3	1.5	3.4	5.2		6.2	ns	
tPZL		ī	1.4	5.5		6.1	1.5	3.7	5.3		5.9	115	
^t PHZ	OE1 or OE2	OE1 or OE2	~	1.4	5.9		6.2	1.5	3.9	5.6		5.9	ns
tPLZ			OE LOT OE2	1	1.4	5.5		5.8	1.5	3.5	5		5.3

 $[\]overline{\dagger}$ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

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PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_I includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_{O} = 50 \,\Omega$, $t_{r} \leq 2.5 \,\text{ns}$, $t_{f} \leq 2.5 \,\text{ns}$.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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